## IN THE SPECIFICATION:

The specification as amended below with replacement paragraphs shows added text with <u>underlining</u> and deleted text with <u>strikethrough</u>.

Please REPLACE paragraph [0036] on page 8 with the following amended paragraph:

**[0036]** The electron donor material is one of an aromatic, an olefin, an allene, a thiophene and a fulvalene heterocyclic compound containing hydrogen, an alkyl group, a phenyl group, an NR<sub>2</sub> group, an OR group and a-an\_SiR<sub>3</sub> group, or one or more electron donor materials selected from the group consisting of poly(3,4-ethylene-dioxythiophene), tetraphenylethylene, azulene, 1,2,3,4-tetraphenyl-1,3-cyclophentadiene, and bis(ethylenedithio)tetrathiafulvalene.

Please REPLACE paragraph [0053] on pages 10 and 11 with the following amended paragraph:

[0053] HTL (BFE manufactured by DOW CHEMICAL CORPORATION) was spin coated on the cooled HIL coated test cells to a thickness of 20, 80, 140 and 200 nm at a predetermined spin coating speed after sufficiently cooling the dried HIL coated test cells so that the HIL spin coated test cells were dried again at a temperature of 200°C for 5 minutes, wherein 2,4-dinitroaniline was mixed with the HTL in a concentration of 1, 3 and 5 wt%. A red low molecular weight molecule (Red Depant:CBP:UDC-Dopant in CBP manufactured by UDC CORPORATION) was used as an emitting layer, and the red low molecular weight molecule (Red Depant:CBP:UDC-Dopant in CBP manufactured by UDC CORPORATION) was coated to a thickness of 22 nm using deposition equipment. Balq (5 nm), Alq3-ALQ3 (20 nm), LiF (8 nm) and AI (250 nm) were sequentially deposited on the emitting layer, and the Balq (5 nm), Alq3
ALQ3 (20 nm), LiF (8 nm) 406 and AI (250 nm) were sealed using moisture absorbing material and a glass cover.